inter_{sil}

IS-1715ARH, IS-1715AEH

Radiation Hardened Complementary Switch FET Drivers

The radiation hardened IS-1715ARH and IS-1715AEH are high speed, high current, complementary power FET drivers designed for use in synchronous rectification circuits. Soft switching transitions for the two output waveforms can be managed by setting the independently programmable delays. Alternatively, the delay pins can be configured for zero-voltage sensing to allow for precise switching control.

The IS-1715ARH and IS-1715AEH have a single input, which is PWM and TTL compatible, and can run at frequencies up to 1MHz. The AUX output switches immediately at the rising edge of the INPUT, but waits for the T2 delay before responding to the falling edge. A logic low on the enable pin (ENBL) places both outputs into an active-low mode, and an Undervoltage Lockout (UVLO) function is set at 9V (maximum).

These devices are constructed with the dielectrically isolated Rad Hard Silicon Gate (RSG) process and are immune to Single Event Latch-Up (SEL). They have been specifically designed to provide highly reliable performance in harsh radiation environments.

Features

- Electrically screened to SMD #5962-00521
- QML qualified per MIL-PRF-38535 requirements
- Radiation environment
 - Gamma dose 3x10⁵rad(Si)
 - Latch-up immune
- PWR output current (source and sink): 3A (peak)
- AUX output current (source and sink): 3A (peak)
- Low operating supply current: 6mA (max)
- Wide programmable delay range: 100ns to 600ns
- Configurable for zero-voltage switching
- Switching frequency to 1MHz
- Both outputs active-low in Sleep mode
- 9V (maximum) UVLO

Related Literature

For a full list of related documents, visit our website:

• IS-1715ARH, IS-1715AEH device pages

Applications

· Synchronous rectification in power supplies

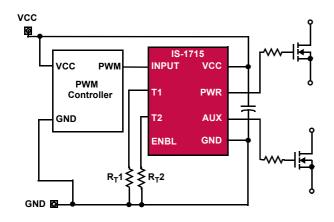


Figure 1. IS-1715 Typical Application Diagram

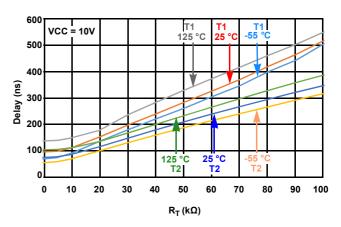
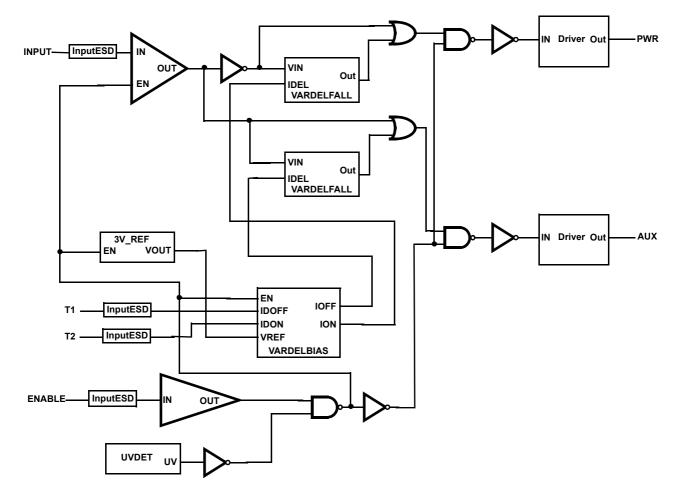


Figure 2. T1 Delay, T2 Delay vs $\rm R_{\rm T}$ vs Temperature

1. Overview

1.1 Functional Block Diagram



Note: VCC and VSS (GND) connections not shown.

Figure 3. Functional Block Diagram

1.2 Ordering Information

| Ordering SMD Number (<u>Note 1</u>) | Part Number (<u>Note 2</u>) | Temp. Range (°C) | Package (RoHS Compliant) | Pkg. Dwg. # |
|--|--|---------------------|-----------------------------|-------------|
| 5962F0052101VXC | IS9-1715ARH-Q | -55 to +125 | 16 Ld Flatpack | K16.A |
| 5962F0052101QXC | IS9-1715ARH-8 | -55 to +125 | 16 Ld Flatpack | K16.A |
| 5962R0052101TXC | IS9-1715ARH-T | -55 to +125 | 16 Ld Flatpack | K16.A |
| 5962F0052101V9A | IS0-1715ARH-Q (<u>Note 3</u>) | -55 to +125 | Die | N/A |
| N/A | IS0-1715ARH/SAMPLE (<u>Notes 3, 4</u>) | -55 to +125 | Die | N/A |
| N/A | IS9-1715ARH/PROTO (Note 4) | -55 to +125 | 16 Ld Flatpack | K16.A |
| 5962F0052103VXC | IS9-1715AEH-Q | -55 to +125 | 16 Ld Flatpack | K16.A |
| 5962F0052103V9A | IS0-1715AEH-Q (<u>Note 3</u>) | -55 to +125 | Die | N/A |

Notes:

1. Specifications for Rad Hard QML devices are controlled by the Defense Logistics Agency Land and Maritime (DLA). The SMD numbers listed must be used when ordering.

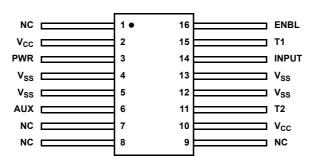
2. These Pb-free Hermetic packaged products employ 100% Au plate - e4 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations.

 Die product tested at T_A = + 25°C. The wafer probe test includes functional and parametric testing sufficient to make the die capable of meeting the electrical performance outlined in <u>"Electrical Specifications" on page 5</u>.

4. The /PROTO and /SAMPLE are not rated or certified for Total Ionizing Dose (TID) or Single Event Effect (SEE) immunity. These parts are intended for engineering evaluation purposes only. The /PROTO parts meet the electrical limits and conditions across the temperature range specified in the DLA SMD and are in the same form and fit as the qualified device. The /SAMPLE die is capable of meeting the electrical limits and conditions specified in the DLA SMD at +25°C only. The /SAMPLE is a die and does not receive 100% screening across the temperature range to the DLA SMD electrical limits. These part types do not come with a certificate of conformance because there is no radiation assurance testing and they are not DLA qualified devices.

1.3 Pin Configuration





1.4 Pin Description

| Pin Number | Pin Name | Description |
|-------------|-----------------|--|
| 1, 7, 8, 9 | NC | No connection. |
| 2, 10 | V _{CC} | Chip positive supply (10V to 18V). |
| 3 | PWR | Output. PWR switches immediately (neglecting propagation delay) at INPUT's falling edge but is delayed after the rising edge by the value of the resistance on T1. PWR is capable of sinking and sourcing 3.0A of peak gate drive current. During sleep mode, PWR is active low. |
| 4, 5, 12,13 | V _{SS} | Chip negative supply (ground connection). |
| 6 | AUX | Output. AUX switches immediately (neglecting propagation delay) at INPUT's rising edge but is delayed after the falling edge before switching by the value of the resistance on T2. AUX is capable of sinking and sourcing 3.0A of peak gate drive current. During sleep mode, AUX is active low. |
| 11 | T2 | Input. A resistor to ground programs the time delay between PWR switch turn-off and AUX turn-on. |
| 14 | INPUT | Input. INPUT switches at TTL logic levels but the allowable range is from 0V to VCC, allowing direct connection to most common IC PWM controller outputs. The rising edge immediately switches the AUX output, and initiates a timing delay, T1, before switching on the PWR output. Similarly, the INPUT falling edge immediately turns off the PWR output and initiates a timing delay, T2, before switching the AUX output. |
| 15 | T1 | Input. A resistor to ground programs the time delay between AXU switch turn-off and PWR turn-on. |
| 16 | ENBL | Input. The ENABLE input switches at TTL logic levels, but the allowable range is from 0 to VCC. The ENABLE input places the device into sleep mode when it is a logic low. The current into VCC during sleep mode is typically 500μ A. |
| N/A | LID | No connection (floating). |

2. Specifications

2.1 Absolute Maximum Ratings

| Parameter | Minimum | Maximum | Unit | |
|--------------------------------------|---------|---------|------|--|
| Supply Voltage Range (VCC) | 10 | 20 | VDC | |
| DC Input Voltage Range (INPUT, ENBL) | 0 | VCC | VDC | |

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions can adversely impact product reliability and result in failures not covered by warranty.

2.2 Thermal Information

| Thermal Resistance (Typical) | θ _{JA} (°C/W) | θ _{JC} (°C/W) |
|--|------------------------|------------------------|
| 16 Ld FP Package (<u>Notes 5, 6</u>) | 90 | 18 |

Notes:

5. θ_{JA} is measured with the component mounted to a high effective thermal conductivity test board in free air. See <u>TB379</u> for details.

6. For $\theta_{JC},$ the "case temp" location is the center of the ceramic on the package underside.

| Parameter | Minimum | Maximum | Unit |
|---|---------|---------|------|
| Lead Temperature (soldering, 10 seconds) | | +265 | °C |
| Maximum Junction Temperature (T _{JMAX}) | | +175 | °C |
| Storage Temperature Range | -65 | +150 | °C |

2.3 Recommended Operating Conditions

| Parameter | Minimum | Maximum | Unit |
|----------------------------|---------|---------|------|
| Supply Voltage Range (VCC) | 10 | 18 | VDC |
| Temperature Range | -55 | +125 | °C |

2.4 Electrical Specifications

 V_{CC} = 10V to 18V, ENBL ≥ 3V, Limits apply over the operating temperature range, -55°C to +125°C unless otherwise specified.

| Description | Parameter | Test Conditions | Min (<u>Note 7</u>) | Тур | Max (<u>Note 7</u>) | Unit |
|----------------------------------|------------------------------------|--|--------------------------|-----|--------------------------|------|
| Overall | | | | | | |
| Operating Voltage Range | V _{CC} | | 10 | - | 18 | V |
| Input Current, Nominal | I _{CC} | ENBL = 3.0V | 1.0 | - | 6.0 | mA |
| Input Current, Sleep Mode | I _{CCS} | ENBL = 0.8V | 300 | - | 900 | μA |
| Under Voltage, Rising Threshold | UV+ | | 8.5 | - | 9.5 | V |
| Under Voltage, Falling Threshold | UV- | | 7.7 | - | 8.8 | V |
| Under Voltage Delta | UVD | | 0 | - | 2.0 | V |
| Power Driver (PWR) | | | | | | |
| Pre Turn-On PWR Output, Low | V _{PPWR} | V_{CC} = 0V, ENBL ≤ 0.8V, I_{OUT} = 10mA | - | - | 2.0 | V |
| PWR Pin Output Low, Saturation | V _{PWR} | INPUT = 0.8V, I _{OUT} = 40mA | - | - | 1.0 | V |
| | | INPUT = 0.8V, I _{OUT} = 100mA | - | - | 1.5 | V |
| PWR Pin Output High, Saturation | V _{CC -} V _{PWR} | INPUT = 3.0V, I _{OUT} = -40mA | - | - | 1.0 | V |
| | | INPUT = 3.0V, I _{OUT} = -100mA | - | - | 1.5 | V |
| Rise Time | t _{RP} | C _L = 2200pF | 15 | - | 50 | ns |

| Description | Parameter | Test Conditions | Min (<u>Note 7</u>) | Тур | Max (<u>Note 7</u>) | Unit |
|---|------------------------------------|---|--------------------------|-----|--------------------------|---------|
| Fall Time | t _{FP} | C _L = 2200pF | 15 | - | 50 | ns |
| T1 Input Pin Delay, AUX to PWR | t _{T1} | INPUT Rising Edge, R _{T1} = 10kΩ, (<u>Figure 4)(Note 8</u>) | 45 | - | 200 | ns |
| | | INPUT Rising Edge, R _{T1} = 100kΩ, (<u>Figure 4)(Note 8</u>) | 250 | - | 1300 | ns |
| PWR Propagation Delay | t _{DP} | INPUT Falling Edge, 50% Points, (<u>Figure 4)(Note 9</u>) | 50 | - | 300 | ns |
| Auxiliary (AUX) | | | | | | |
| AUX Pre Turn-On AUX Output, Low | V _{PAUX} | V_{CC} = 0V, ENBL ≤ 0.8V, I_{OUT} = 10mA | - | - | 2.0 | V |
| AUX Pin Output Low, Saturation | V _{AUX} | INPUT = 3.0V, I _{OUT} = 40mA | - | - | 1.0 | V |
| | | INPUT = 3.0V, I _{OUT} = 100mA | - | - | 1.5 | V |
| AUX Pin Output High, Saturation | V _{CC -} V _{AUX} | INPUT = 0.8V, I _{OUT} = -40mA | - | - | 1.0 | V |
| | | INPUT = 0.8V, I _{OUT} = -100mA | - | - | 1.5 | V |
| Rise Time | t _{RP} | C _L = 2200pF | 15 | - | 50 | ns |
| Fall Time | t _{FP} | C _L = 2200pF | 15 | - | 50 | ns |
| T2 Input Pin Delay, PWR to AUX | t _{T2} | INPUT Falling Edge, $R_{T2} = 10k\Omega$, (<u>Figure 4</u>)(<u>Note 8</u>) | 50 | - | 130 | ns |
| | | INPUT Rising Edge, R _{T2} = 100kΩ, (<u>Figure 4</u>)(<u>Note 8</u>) | 200 | - | 700 | ns |
| AUX Propagation Delay | t _{DA} | INPUT Rising Edge at 50% Points, (<u>Figure 4)(Note 9</u>) | 50 | - | 185 | ns |
| Enable (ENBL) | | • | | | | |
| Input Threshold Voltage | V _{IT} | | - | - | 2.8 | V |
| Input Current High | I _{IH} | ENABLE = 15V | -10 | - | 10 | μA |
| Input Current Low | I _{IL} | ENABLE = 0V | -15 | - | 15 | μA |
| T1 Input | | • | | | | |
| Current Limit | T _{1CL} | T1 Input = 0V | -5.5 | - | -1.6 | mA |
| Nominal Voltage at T1 Pin | T _{1NV} | | 2.7 | - | 3.3 | V |
| Minimum T1 Pin Delay | T _{1DM} | T1 Pin = 2.5V | 25 | - | 120 | ns |
| T2 Input | | | · | • | ·I | |
| Current Limit | T _{2CL} | T2 Input = 0V | -5.5 | - | -2.1 | mA |
| Nominal Voltage at T2 Pin | T _{2NV} | | 2.7 | - | 3.3 | V |
| Minimum T2 Pin Delay | T _{2DM} | T1 Pin = 2.5V | 20 | - | 80 | ns |
| Input | 1 | | I | | | |
| | | | | | | |
| Input Threshold Voltage | V _{IT} | | - | - | 2.8 | V |
| Input Threshold Voltage Input Current High | V _{IT} | ENABLE = 15V | - -10 | - | 2.8 10 | v µA |

 V_{CC} = 10V to 18V, ENBL ≥ 3V, Limits apply over the operating temperature range, -55°C to +125°C unless otherwise specified. (Continued)

Notes:

7. Parameters with MIN and/or MAX limits are 100% tested at -55°C, +25°C, and +125°C, unless otherwise specified.

8. T1 delay and T2 delay are defined as the time between the 50% transition point of AUX (PWR) and the 50% transition point of PWR (AUX) with no capacitive load on either output (Figure 4).

 Propagation delays (t_{DP} and t_{DA}) are measured from the 50% point of the input signal to the 50% point of the output signal's transition with no load on the outputs (<u>Figure 4</u>).

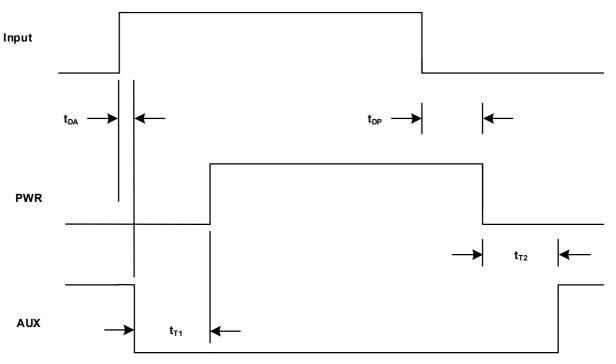
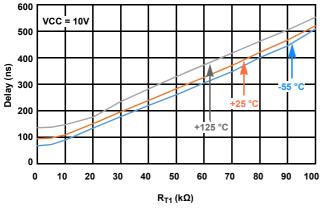


Figure 4. Timing Diagram

3. Typical Performance Curves





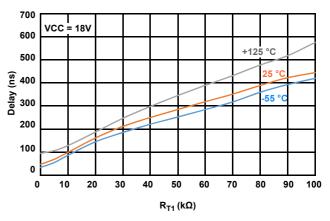


Figure 6. T1 Delay vs R_{T1} vs Temperature

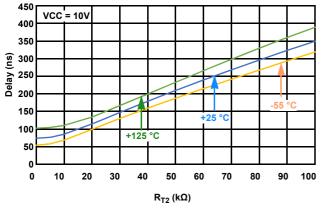


Figure 7. T2 Delay vs R_{T2} vs Temperature

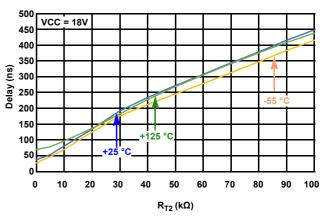
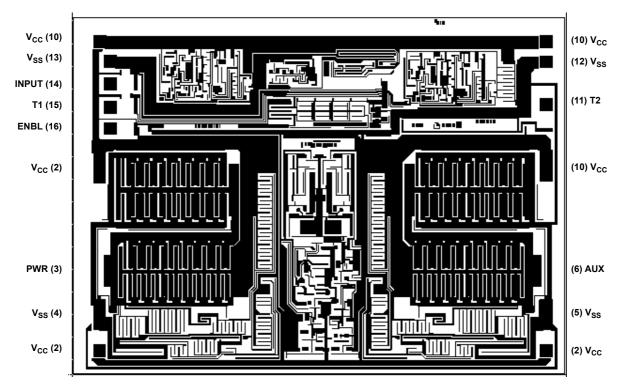


Figure 8. T2 Delay vs R_{T2} vs Temperature

4. Die Characteristics

| Die Information | |
|------------------------------|--|
| Die Dimensions | 3559μm x 4420μm (129 mils x 174 mils) Thickness: 483μm ±25.4μm (19 mils ±1 mil) |
| Interface Materials | |
| Glassivation | Type: Phosphorus Silicon Glass (PSG) Thickness: 8.0kÅ ± 1.0kÅ |
| Top Metallization | Type: AlSiCu Thickness: 16.0kÅ ± 2kÅ |
| Substrate | Radiation Hardened Silicon Gate, Dielectric Isolation |
| Backside Finish | Silicon |
| Assembly Related Information | · · · · |
| Substrate Potential | Unbiased (DI) |
| Additional Information | |
| Worst Case Current Density | <2.0 x 10 ⁵ A/cm ² |
| Transistor Count | 222 |

4.1 Metallization Mask Layout



Notes:

10. All double-sized pads should be double bonded.

11. All Pin 2 and Pin 10 VCC pads are bonded to VCC for power and noise considerations (these are lead-frame connected in packaged devices).

5. Revision History

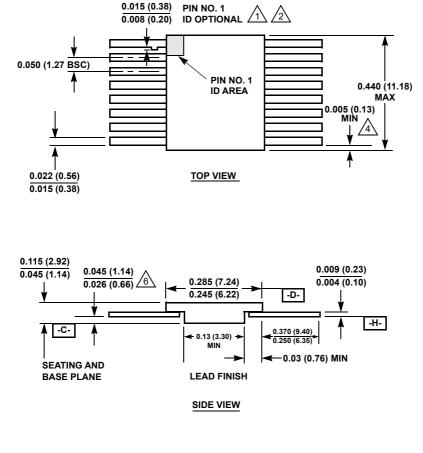
| Rev. | Date | Description |
|------|-----------|--|
| 5.0 | Feb.4.21 | Updated Figure 4. |
| 4.0 | Jul.22.20 | On page 3, Section 1.4 Pin Description Table added new row for the "LID". On page 7, corrected Figure 4, Timing Diagram. |
| 3.0 | Aug.16.19 | Updated to new format. Updated links throughout document Updated Ordering information table by correcting package information for IS0-1715ARH/SAMPLE. Updated Disclaimer. |
| 2.0 | Dec.21.17 | On page 1, added Figure 1 and Figure 2. On page 2, added Functional Block Diagram. On page 4, added table of Pin Descriptions On page 5, added Absolute Maximum Ratings, Thermal Information, and Recommended Operating Conditions. On page 6 and 7, added Electrical Specifications. On page 7, added Timing Diagram. On page 8, added Typical Performance Curves. |
| 1.0 | Aug.23.17 | Updated to new format. On page 1, added Related Literature. Ordering Information table: Added IS9-1715ARH-T, IS0-1715ARH-Q, IS0-1715ARH/SAMPLE, IS9-1715AEH-Q and IS0-1715AEH-Q Added Package and Pkg Dwg columns Added Notes 1, 2, 3 Added Revision History table, POD K16.A, and About Intersil. |

6. Package Outline Drawing

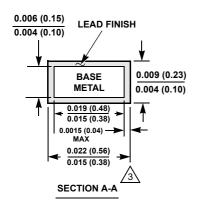
For the most recent package outline drawing, see K16.A.

K16.A

16 LEAD CERAMIC METAL SEAL FLATPACK PACKAGE Rev 2, 1/10







- 1. Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark. Alternately, a tab may be used to identify pin one.
- 2. If a pin one identification mark is used in addition to a tab, the limits of the tab dimension do not apply.
- 3. The maximum limits of lead dimensions (section A-A) shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.
- 4. Measure dimension at all four corners.
- 5. For bottom-brazed lead packages, no organic or polymeric materials shall be molded to the bottom of the package to cover the leads.
- 6. Dimension shall be measured at the point of exit (beyond the meniscus) of the lead from the body. Dimension minimum shall be reduced by 0.0015 inch (0.038mm) maximum when solder dip lead finish is applied.
- 7. Dimensioning and tolerancing per ANSI Y14.5M 1982.
- 8. Controlling dimension: INCH.

IMPORTANT NOTICE AND DISCLAIMER

RENESAS ELECTRONICS CORPORATION AND ITS SUBSIDIARIES ("RENESAS") PROVIDES TECHNICAL SPECIFICATIONS AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS OR IMPLIED, INCLUDING, WITHOUT LIMITATION, ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for developers skilled in the art designing with Renesas products. You are solely responsible for (1) selecting the appropriate products for your application, (2) designing, validating, and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. Renesas grants you permission to use these resources only for development of an application that uses Renesas products. Other reproduction or use of these resources is strictly prohibited. No license is granted to any other Renesas intellectual property or to any third party intellectual property. Renesas disclaims responsibility for, and you will fully indemnify Renesas and its representatives against, any claims, damages, costs, losses, or liabilities arising out of your use of these resources. Renesas' products are provided only subject to Renesas' Terms and Conditions of Sale or other applicable terms agreed to in writing. No use of any Renesas resources expands or otherwise alters any applicable warranties or warranty disclaimers for these products.

(Rev.1.0 Mar 2020)

Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan www.renesas.com

Trademarks

Renesas and the Renesas logo are trademarks of Renesas Electronics Corporation. All trademarks and registered trademarks are the property of their respective owners.

Contact Information

For further information on a product, technology, the most up-to-date version of a document, or your nearest sales office, please visit: www.renesas.com/contact/